Manzar Siddik

List of Publications by Year
in descending order

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16	308	759233 12	996975 15
papers	citations	h-index	g-index

16	16	16	486
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Physics-Based Compact Model of Stochastic Switching in Spin-Transfer Torque Magnetic Memory. IEEE Transactions on Electron Devices, 2019, 66, 4176-4182.	3.0	10
2	Modeling of Breakdown-Limited Endurance in Spin-Transfer Torque Magnetic Memory Under Pulsed Cycling Regime. IEEE Transactions on Electron Devices, 2018, 65, 2470-2478.	3.0	19
3	Random Number Generation by Differential Read of Stochastic Switching in Spin-Transfer Torque Memory. IEEE Electron Device Letters, 2018, 39, 951-954.	3.9	19
4	A nitrogen-treated memristive device for tunable electronic synapses. Semiconductor Science and Technology, 2014, 29, 104006.	2.0	10
5	Selfâ€formed Schottky barrier induced selectorâ€less RRAM for crossâ€point memory applications. Physica Status Solidi - Rapid Research Letters, 2012, 6, 454-456.	2.4	31
6	Highly uniform and reliable resistance switching properties in bilayer WO_x/NbO_x RRAM devices. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1179-1183.	1.8	37
7	Operation Voltage Control in Complementary Resistive Switches Using Heterodevice. IEEE Electron Device Letters, 2012, 33, 600-602.	3.9	15
8	Thermally-assisted Ti/Pr<inf>0.7</inf>Ca<inf>0.3</inf>MnO<inf>3</inf> ReRAM with excellent switching speed and retention characteristics. , 2011, , .		5
9	Low temperature solution-processed graphene oxide/Pr0.7Ca0.3MnO3 based resistive-memory device. Applied Physics Letters, 2011, 99, .	3.3	42
10	Effect of $hbox{Ge}_{2}hbox{Sb}_{2}hbox{Te}_{5}$ Thermal Barrier on Reset Operations in Filament-Type Resistive Memory. IEEE Electron Device Letters, 2011, 32, 1573-1575.	3.9	13
11	Noise-Analysis-Based Model of Filamentary Switching ReRAM With $hbox{ZrO}_{x}/hbox{HfO}_{x}$ Stacks. IEEE Electron Device Letters, 2011, 32, 964-966.	3.9	33
12	Memristive switching behavior in Pr_{0.7}Ca_{0.3}MnO₃ by incorporating an oxygenâ€deficient layer. Physica Status Solidi - Rapid Research Letters, 2011, 5, 409-411.	2.4	19
13	Improved switching characteristics of perovskite oxideâ€based resistance random access memory by highâ€pressure oxygen annealing at low temperature. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 202-205.	1.8	5
14	Excellent resistive switching in nitrogen-doped Ge2Sb2Te5 devices for field-programmable gate array configurations. Applied Physics Letters, 2011, 99, 192110.	3.3	21
15	Thermally assisted resistive switching in Pr0.7Ca0.3MnO3/Ti/Ge2Sb2Te5 stack for nonvolatile memory applications. Applied Physics Letters, 2011, 99, .	3.3	14
16	Effect of interfacial oxide layer on the switching uniformity of Ge2Sb2Te5-based resistive change memory devices. Applied Physics Letters, 2011, 99, 162109.	3.3	15